

In the SpecificationPlease amend paragraph 0009 as follows:

Referring to Fig. 2b, ~~a sidewall-an oxide layer 24 is provided to prevent the substrate from being damaged during the etching process is deposited on the resulting substrate 10.~~

Please amend paragraph 0014 as follows:

As disclosed herein, one example method may include forming a gate oxide and a gate electrode on a semiconductor substrate, performing a first ion implantation process for the formation of an LDD region in the substrate, forming spacers on the sidewalls of the gate electrode, and performing a second ion implantation process for the formation of a junction region in the substrate using the spacers as a mask. The example method may also include forming a trench for device isolation by removing selectively the top portion of the substrate between the spacers, forming a sidewall oxide layer on the resulting substrate, forming a diffusion barrier on the ~~sidewall-oxide layer~~, and depositing a gap filling insulation layer over the diffusion barrier. The disclosed example method may further include planarizing the gap filling insulating layer and removing selectively some part of the gap filling insulation layer to form contact holes.